

(3)

SSCN3904GS8

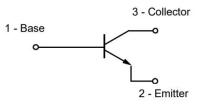
NPN Switching Transistor

\triangleright Features

| VCB | VCE | VBE | VCESAT | IC |
|-----|-----|-----|--------|-------|
| 60 | 40V | 6V | 300mV | 200mA |

Description \succ

The NPN Transistor is designed for use in linear and switching applications. The device is housed in the SOT-523 package, which is designed for telephony and professional СС



Pin configuration

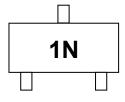
(1)

(2)

SOT-523

 \triangleright

Circuit Diagram



Marking(Top View)

| mon | 10 | doolghod | 101 | torophony | |
|------|-------|--------------|------|-----------|--|
| ommu | nicat | tion equipme | ent. | | |
| | | | | | |

Applications \geq

- General purpose switching and amplification •
- Telephony and professional communication equipment

Ordering Information \geq

| Device | Package | Shipping |
|-------------|---------|-----------|
| SSCN3904GS8 | SOT-523 | 3000/Reel |



> Absolute Maximum Ratings($T_A=25^{\circ}C$ unless otherwise noted)

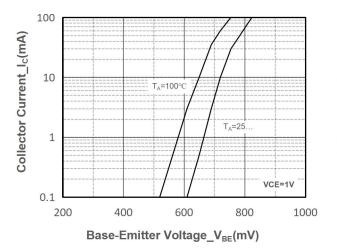
| Parameter | Symbol | Value | Unit |
|------------------------------|------------------|------------|------|
| Collector-Base Voltage | V _{CBO} | 60 | V |
| Collector- Emitter Voltage | Vceo | 40 | V |
| Emitter-Base Voltage | VEBO | 6 | V |
| Collector Current-Continuous | lc | 200 | mA |
| Collector Power Dissipation | Pc | 200 | mW |
| Junction Temperature | TJ | 150 | °C |
| Storage Temperature | T _{STG} | -55 to 150 | °C |

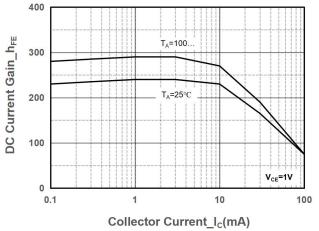
> Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit |
|--------------------------------------|----------------------|--|------|------|------|------|
| Collector-Base Breakdown Voltage | BV _{CBO} | I _C =10uA,I _E =0 | 60 | | | V |
| Collector-emitter Breakdown Voltage | BV _{CEO} | I _C =1mA,I _B =0 | 40 | | | V |
| Emitter -Base Breakdown Voltage | BV _{EBO} | I _E =10uA,I _C =0 | 6 | | | V |
| Collector Cutoff Current | I _{CEX} | V_{CE} =30V, V_{EB} =3V | | | 50 | nA |
| Collector Cutoff Current | I _{СВО} | V _{CB} =30V,I _E =0 | | | 100 | nA |
| Emitter Cutoff Current | Іево | V _{EB} =3V,I _C =0 | | | 100 | nA |
| | h _{FE} | V _{CE} =1V,I _C =10mA | 100 | | 300 | |
| DC Current Gain | | V _{CE} =1V,I _C =0.1mA | 40 | | | |
| | | V _{CE} =1V,I _C =100mA | 30 | | | |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | I _C =50mA,I _B =5mA | | | 0.3 | V |
| Base-Emitter Saturation Voltage | V _{BE(sat)} | Ic=50mA,I _B =5mA | | | 0.95 | V |
| Transition frequency | fT | V _{CE} =20V,Ic=10mA f=100MHz | 250 | | | MHz |
| Delay Time | t _d | V _{CC} =3V,V _{BE(off)} =-0.5V I _C =10mA,I _{B1} =1mA | | | 35 | ns |
| Rise Time | tr | $V_{CC}=3V, V_{BE(off)}=-0.5V$ $I_{C}=10mA, I_{B1}=1mA$ | | | 35 | ns |
| Storago Timo | ts | V _{CC} =3V,I _C =10mA | | | 200 | ns |
| Storage Time | | I _{B1} = I _{B2} =1mA | | | 200 | |
| Fall Time | t _f | V _{CC} =3V,I _C =10mA | | | 50 | ns |
| | | I _{B1} = I _{B2} =1mA | | | | |

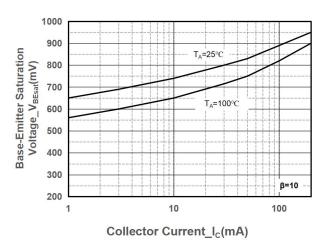


> Typical Performance Characteristics (T_A=25°C unless otherwise noted)

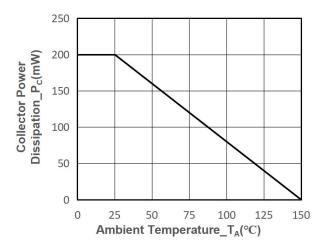




Collector Current vs. Base-Emitter Voltage

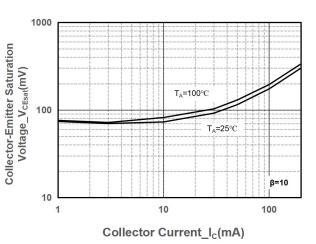




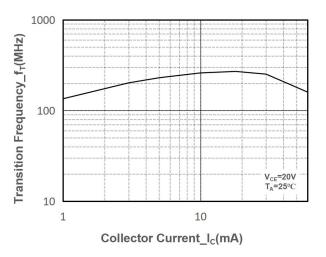


Power derating vs. Ambient temperature

DC Current Gain vs. Collector Current



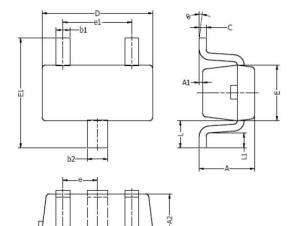
V_{CE(sat)} vs. Collector Current



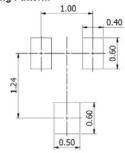
Transition Frequency vs. Collector Current



Package Information







| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.70 | 0.90 | 0.028 | 0.035 |
| A1 | 0.00 | 0.10 | 0.000 | 0.004 |
| A2 | 0.70 | 0.80 | 0.028 | 0.031 |
| b1 | 0.15 | 0.25 | 0.006 | 0.010 |
| b2 | 0.25 | 0.35 | 0.010 | 0.014 |
| с | 0.10 | 0.20 | 0.004 | 0.008 |
| D | 1.50 | 1.70 | 0.059 | 0.067 |
| E | 0.70 | 0.90 | 0.028 | 0.035 |
| E1 | 1.45 | 1.75 | 0.057 | 0.069 |
| е | 0.50 TYP. | | 0.020 | TYP. |
| e1 | 0.90 | 1.10 | 0.035 | 0.043 |
| L | 0.40 REF. | | 0.016 | REF. |
| L1 | 0.10 | 0.30 | 0.004 | 0.012 |
| θ | 0° | 8° | 0° | 8° |

NOTES: 1. Above package outline conforms to JEITA EAIJ ED-7500A SC-75A. 2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

SOT-523



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